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Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	09/256643
Filing Date	February 23, 1999
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Trinh, Michael

Sheet 1 of 2

Attorney Docket No: 00303.324US2

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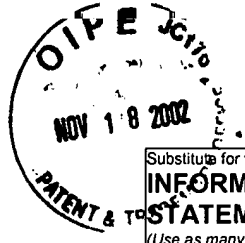
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Michael Trinh

DATE CONSIDERED

1/24/02



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PTO/SB/08A(10-01)
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Sheet 2 of 2		Attorney Docket No: 00303.324US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Substitute Disclosure Statement Form (PTO-1449)
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